

PROTECTION PRODUCTS

Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{pk}	40	Watts
Maximum Peak Pulse Current ($t_p = 8/20\mu s$)	I_{pp}	5	Amps
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{pp}	+/- 20 +/- 15	kV
Operating Temperature	T_J	-55 to +125	°C
Storage Temperature	T_{STG}	-55 to +150	°C

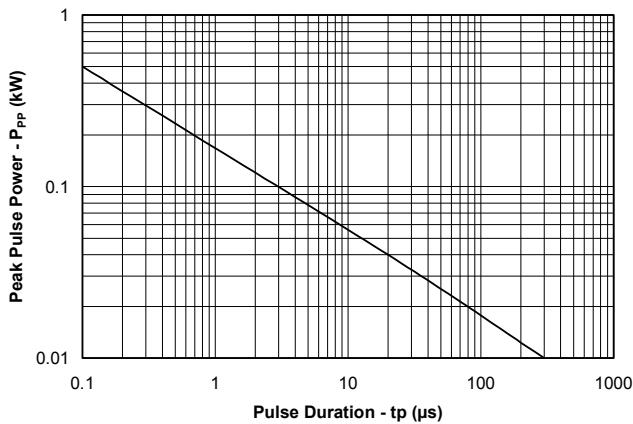
Electrical Characteristics (T=25°C)

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V_{RWM}				3.3	V
Punch-Through Voltage	V_{PT}	$I_{PT} = 2\mu A$	3.5			V
Snap-Back Voltage	V_{SB}	$I_{SB} = 50mA$	2.8			V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3V$		0.05	0.5	μA
Clamping Voltage	V_C	$I_{pp} = 1A$, $t_p = 8/20\mu s$ Any I/O to Gnd			5.5	V
Clamping Voltage	V_C	$I_{pp} = 5A$, $t_p = 8/20\mu s$ Any I/O to Gnd			8.0	V
Reverse Clamping Voltage	V_{CR}	$I_{pp} = 1A$, $t_p = 8/20\mu s$ Any I/O to Gnd			2.4	V
Junction Capacitance	C_J	I/O pin to Gnd $V_R = 0V$, $f = 1MHz$		25	30	pF
		I/O pin to Gnd $V_R = 3.3V$, $f = 1MHz$		14		pF

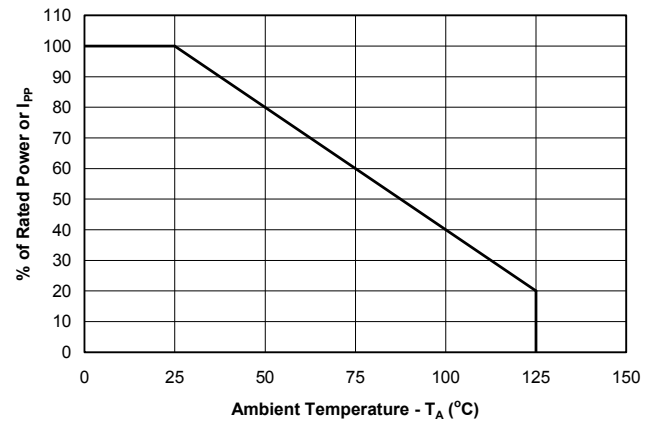
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Typical Characteristics

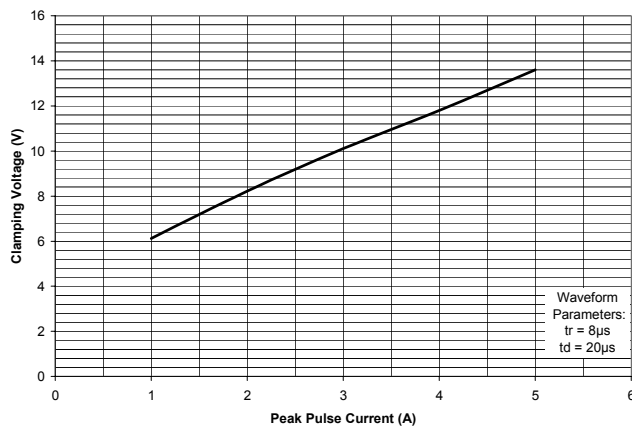
Non-Repetitive Peak Pulse Power vs. Pulse Time



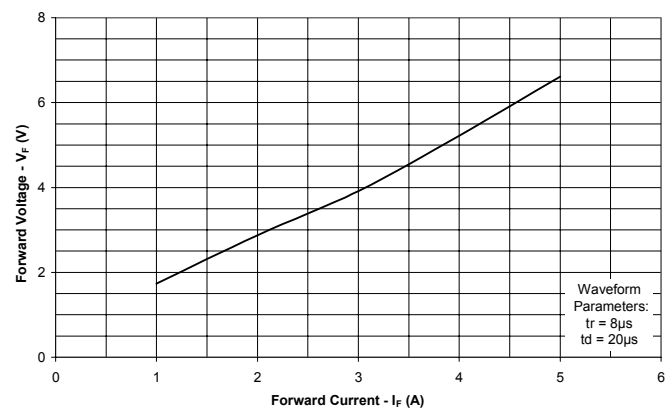
Power Derating Curve



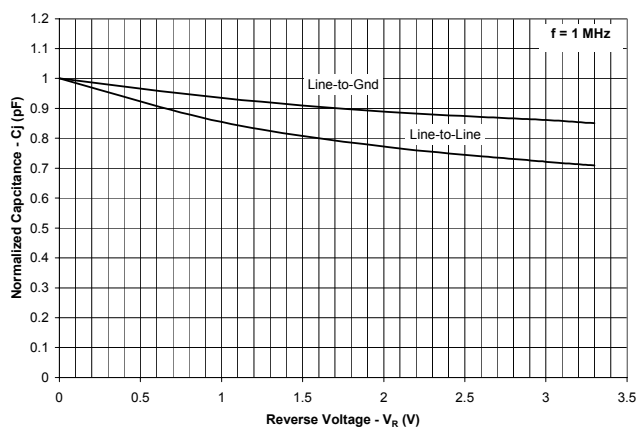
Clamping Voltage vs. Peak Pulse Current



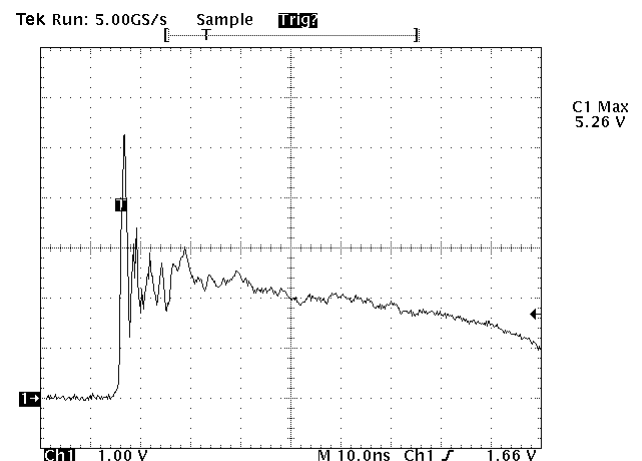
Forward Voltage vs. Forward Current



Junction Capacitance vs. Reverse Voltage



ESD Clamping (8kV Contact per IEC 61000-4-2)



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Applications Information

Device Connection Options

The μ Clamp3324P is designed to protect four lines. It will present a high impedance to the protected line up to 3.3 volts. It will “turn on” when the line voltage exceeds 3.5 volts. The device is unidirectional and may be used on lines where the signal polarity is above ground.

Flow Thru Layout

The μ Clamp3324P is designed for ease of PCB layout by allowing the traces to enter one side of the device and exit the other side. Figure 2 shows the recommended way to design the PCB board traces in order to use the flow through layout. The solid line represents the PCB trace. Note that the PCB traces enter at the input pin and exit from the opposite pin. (pin 1 to pin 8, pin 2 to pin 9, pin 3 to pin 6, pin 4 to pin 5). For example, line 1 enters at pin 1 and exits at Pin 8. The bottom tab is connected to ground. This connection should be made directly to a ground plane on the board for best results. The path length is kept as short as possible to minimize parasitic inductance.

EPD TVS Characteristics

These devices are constructed using Semtech’s proprietary EPD technology. The structure of the EPD TVS is vastly different from the traditional pn-junction devices. At voltages below 5V, high leakage current and junction capacitance render conventional avalanche technology impractical for most applications. However, by utilizing the EPD technology, these devices can effectively operate at 3.3V while maintaining excellent electrical characteristics.

The EPD TVS employs a complex npnp structure in contrast to the pn structure normally found in traditional silicon-avalanche TVS diodes. The EPD mechanism is achieved by engineering the center region of the device such that the reverse biased junction does not avalanche, but will “punch-through” to a conducting state. This structure results in a device with superior DC electrical parameters at low voltages while maintaining the capability to absorb high transient currents.

Figure 1 - Circuit Diagram

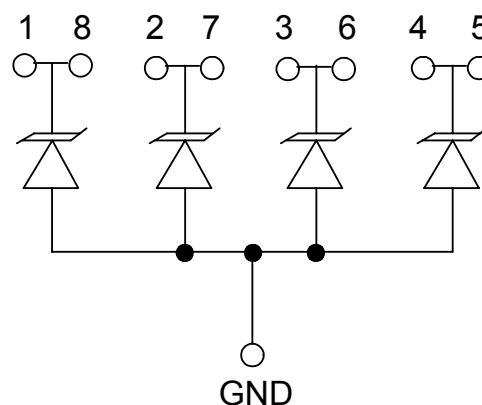


Figure 2 - Layout Example

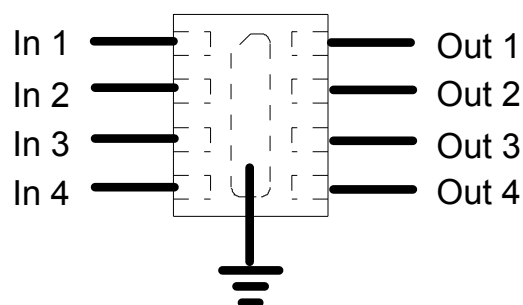
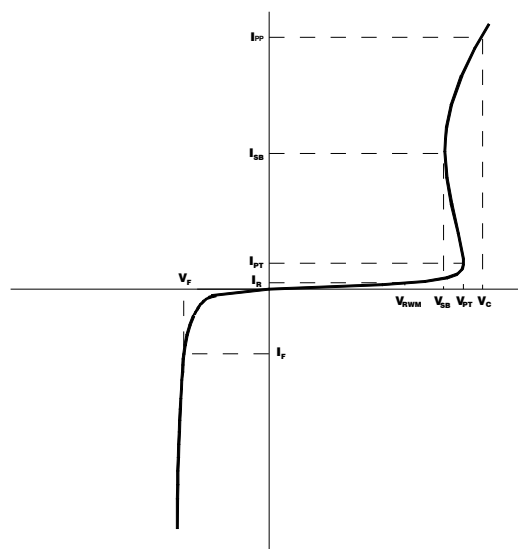
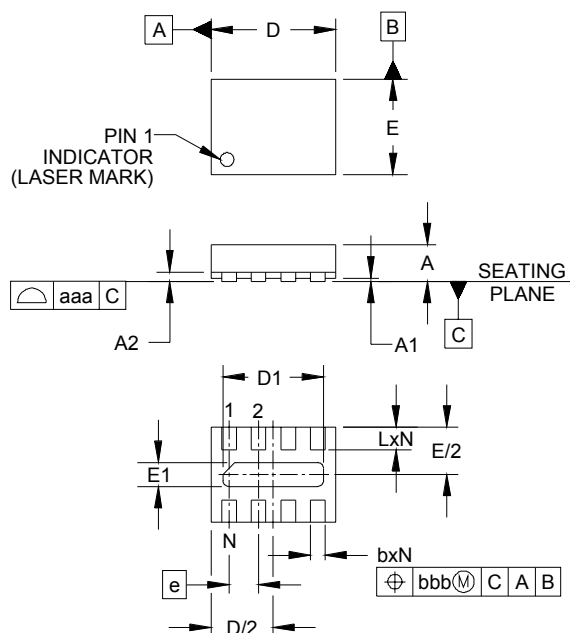


Figure 3 - EPD TVS IV Characteristic Curve

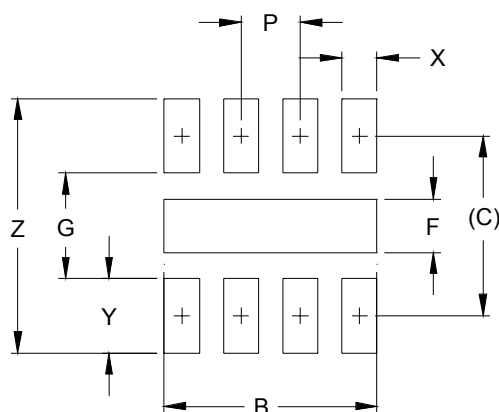


PROTECTION PRODUCTS
Outline Drawing - SLP2116P8


DIM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.020	.023	.026	0.50	0.58	0.65
A1	-	.001	.002	0.00	.003	0.05
A2	-	(.006)	-	-	(0.15)	-
b	.007	.010	.012	0.20	0.25	0.30
D	.079	.083	.087	2.00	2.10	2.20
D1	.061	.067	.071	1.55	1.70	1.80
E	.059	.063	.067	1.50	1.60	1.70
E1	.010	.016	.020	0.25	0.40	0.50
e	.020	BSC	-	0.50	BSC	-
L	.011	.013	.015	0.28	0.33	0.38
N	6	-	-	6	-	-
aaa	.003	-	-	0.08	-	-
bbb	.004	-	-	0.10	-	-

NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

Land Pattern - SLP2116P8


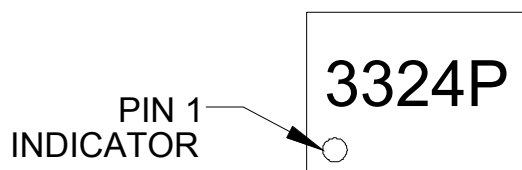
DIM	DIMENSIONS	
	INCHES	MILLIMETERS
B	.071	1.80
C	.060	1.52
F	.018	0.45
G	.035	0.89
P	.020	0.50
X	.012	0.30
Y	.025	0.63
Z	.085	2.15

NOTES:

1. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY.
CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR
COMPANY'S MANUFACTURING GUIDELINES ARE MET.

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Marking

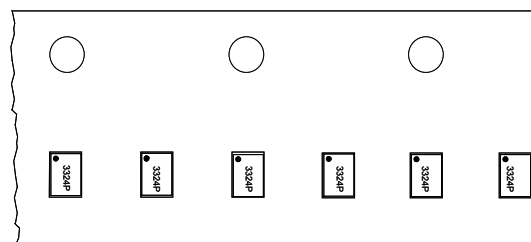
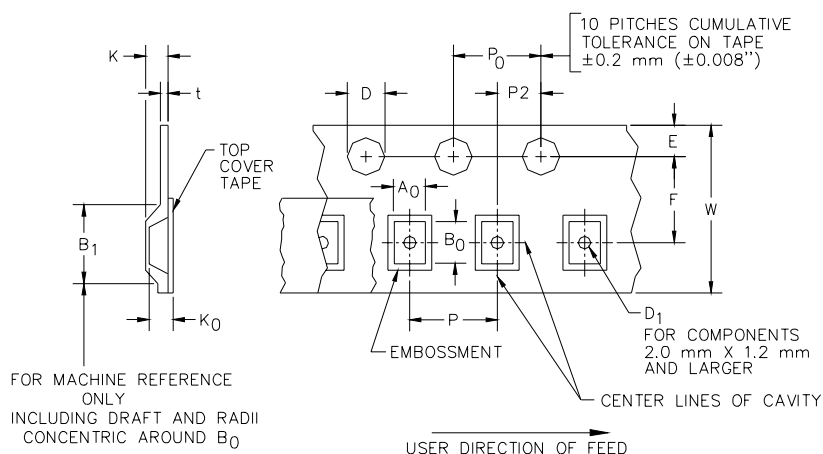


Ordering Information

Part Number	Working Voltage	Device Marking	Qty per Reel	Reel Size
uClamp3324P.TCT	3.3V	3324P	3,000	7 Inch

MicroClamp, uClamp and μ Clamp are marks of Semtech Corporation

Tape and Reel Specification



Device Orientation in Tape

A0	B0	K0
1.96 +/-0.05 mm	2.31 +/-0.05 mm	0.74 +/-0.05 mm

Tape Width	B, (Max)	D	D1	E	F	K (MAX)	P	P0	P2	T(MAX)	W
8 mm	4.2 mm (.165)	1.5 + 0.1 mm - 0.0 mm (0.59 +.005 - .000)	0.8 mm ±0.05 (.031)	1.750±.10 mm (.069±.004)	3.5±0.05 mm (.138±.002)	2.4 mm (.094)	4.0±0.1 mm (.157±.00-4)	4.0±0.1 mm (.157±.00-4)	2.0±0.05mm (.079±.002)	0.4 mm (.016)	8.0 mm + 0.3 mm - 0.1 mm (.312±.012)

Contact Information

Semtech Corporation
Protection Products Division
200 Flynn Road, Camarillo, CA 93012
Phone: (805)498-2111 FAX (805)498-3804